

**IN THE CLAIMS:**

Please cancel claims 1-3 and 6-12 without prejudice.

Kindly amend claim 4 and add new claims 13-16 as follows.

1 -3. (Canceled)

4. (Presently Amended) A method for forming patterns, which comprises the steps of:

applying a photosensitive resin composition onto a substrate and drying;

exposing the composition using ~~i-lines~~ line monochromatic light as a light source ~~by an i-line stepper;~~

developing the composition; and

heating the composition, wherein:

the substrate is a silicon wafer having a diameter of at least 12 inches;

the photosensitive resin composition comprises an aromatic polyimide precursor wherein a 10  $\mu\text{m}$  thick layer of the aromatic polyimide precursor has a light transmittance at a wavelength of 365 nm of at least 1%, and a 10  $\mu\text{m}$  thick polyimide film made from the resin composition by imidation ring closure and deposited on a silicon substrate has a residual stress of at most 25 MPa; ~~wherein and~~

the photosensitive resin composition is selected from the group consisting of (1) a negative-type photosensitive resin composition where the aromatic polyimide precursor comprises a repetitive unit having a monovalent organic group with a carbon-carbon unsaturated double bond on at least a part of side chains of carboxylic acid residues, and (2)

a positive-type photosensitive resin composition where the aromatic polyimide precursor comprises a repetitive unit having a group represented by  $-\text{OR}^6$  or  $-\text{NH-R}^6$  on at least a part of side chains of carboxylic acid residues, provided that  $\text{R}^6$  is a monovalent organic group with no carbon-carbon unsaturated double bond.

5-12. (Canceled)

13. (NEW) The method of claim 4, wherein said photosensitive resin composition comprises an aromatic polyimide precursor soluble in an aqueous alkaline solution, wherein a  $10\text{ }\mu\text{m}$  thick layer of the aromatic polyimide precursor has a light transmittance at a wavelength of 365 nm of at least 1%, and a  $10\text{ }\mu\text{m}$  thick polyimide film made from the resin composition by imidation ring closure and deposited on a silicon substrate has a residual stress of at most 25 MPa, and

wherein said photosensitive resin composition is selected from the group consisting of (1) a negative-type photosensitive resin composition where the aromatic polyimide precursor comprises a repetitive unit having a monovalent organic group with a carbon-carbon unsaturated double bond on at least a part of side chains of carboxylic acid residues, and (2) a positive-type photosensitive resin composition where the aromatic polyimide precursor comprises a repetitive unit having a group represented by  $-\text{OR}^6$  or  $-\text{NH-R}^6$  on at least a part of side chains of carboxylic acid residues, provided that  $\text{R}^6$  is a monovalent organic group with no carbon-carbon unsaturated double bond.

14. (NEW) The method of claim 4, wherein said photosensitive resin composition comprises an aromatic polyimide precursor, wherein a  $10\text{ }\mu\text{m}$  thick layer of the aromatic

polyimide precursor has a light transmittance at a wavelength of 365 nm of at least 1%, and a 10  $\mu\text{m}$  thick polyimide film made from the resin composition by imidation ring closure and deposited on a silicon substrate has a residual stress of at most 25 MPa,

wherein said photosensitive resin composition is selected from the group consisting of (1) a negative-type photosensitive resin composition where the aromatic polyimide precursor comprises a repetitive unit having a monovalent organic group with a carbon-carbon unsaturated double bond on at least a part of side chains of carboxylic acid residues, and (2) a positive-type photosensitive resin composition where the aromatic polyimide precursor comprises a repetitive unit having a group represented by  $-\text{OR}^6$  or  $-\text{NH-R}^6$  on at least a part of side chains of carboxylic acid residues, provided that  $\text{R}^6$  is a monovalent organic group with no carbon-carbon unsaturated double bond, and

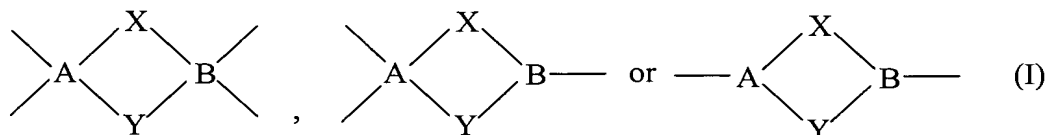
wherein the monovalent organic group of the negative-type photosensitive resin composition is a group represented by  $-\text{O}^-\text{N}^+\text{HR}^4\text{R}^5-\text{R}^7$ , wherein  $\text{R}^4$  and  $\text{R}^5$  each independently represent a hydrocarbon group, and  $\text{R}^7$  represents a monovalent organic group having a carbon-carbon unsaturated double bond.

15. (NEW) The method of claim 13, wherein an amine residue in the repetitive unit of the aromatic polyimide precursor contains an alkali-developable group.

16. (NEW) The method of claim 4, wherein said photosensitive resin composition comprises an aromatic polyimide precursor, wherein a 10  $\mu\text{m}$  thick layer of the aromatic polyimide precursor has a light transmittance at a wavelength of 365 nm of at least 1%, and a 10  $\mu\text{m}$  thick polyimide film made from the resin composition by imidation ring closure and deposited on a silicon substrate has a residual stress of at most 25 MPa,

wherein said photosensitive resin composition is selected from the group consisting of (1) a negative-type photosensitive resin composition where the aromatic polyimide precursor comprises a repetitive unit having a monovalent organic group with a carbon-carbon unsaturated double bond on at least a part of side chains of carboxylic acid residues, and (2) a positive-type photosensitive resin composition where the aromatic polyimide precursor comprises a repetitive unit having a group represented by  $-OR^6$  or  $-NH-R^6$  on at least a part of side chains of carboxylic acid residues, provided that  $R^6$  is a monovalent organic group with no carbon-carbon unsaturated double bond, and

the aromatic polyimide precursor has structural units of the formula (I):



wherein A and B each independently represents a trivalent or tetravalent aromatic group; and X and Y each independently represents an at least divalent group not conjugating with A or B.